WSB5511M

3A Schottky Barrier Diode

Http://www.sh-willsemi.com

Features

- Low forward voltage
- Extremely low thermal resistance
- High current capability



SMA (DO-214AC)



Circuit

Applications

- Switching circuit
- Middle current rectification



Marking

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RRM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current (DC)	I_O	3.0	A
Forward Peak Surge Current (1)	I_{FSM}	50	A
Junction temperature	T_J	-55 ~ 150	°C
Operating temperature	Topr	-55 ~ 150	°C
Storage temperature	Tstg	-55 ~ 150	°C

Electronics characteristics (T_A=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage (2)	V_F	I_F=3.0A			0.50	V
Reverse current	I_R	V_R=40V			0.5	mA
Junction capacitance	C_J	V_R=4V, F=1MHz		220		pF
Thermal resistance	$R_{\theta(J-L)}$	Junction to Lead (Fig.2)		17		K/W

Order Informations

Device	Package	Marking	Shipping
WSB5511M-2/TR	SMA (DO-214AC)	.EC* (3)	5000/Reel&Tape

Note1: Pulse width=8.3ms, single pulse;

Note2: Single Pulse, test Tp=380us;

Note3: * =Month code (A~Z); .EC =Device code;

Typical characteristics (Ta=25°C, unless otherwise noted)

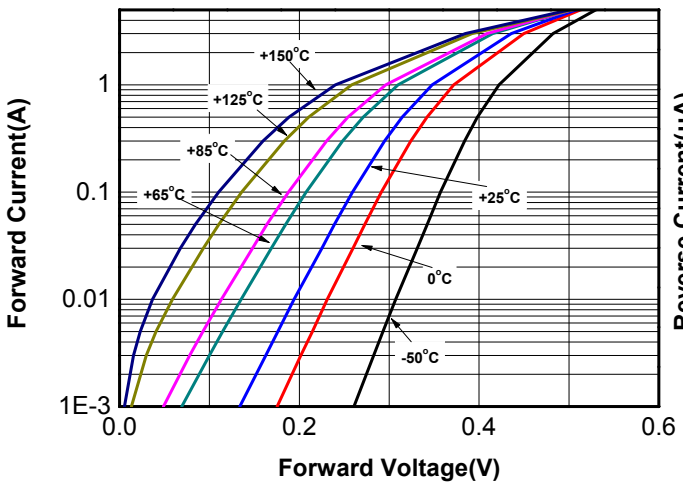


Fig.1 Forward voltage vs. Forward current

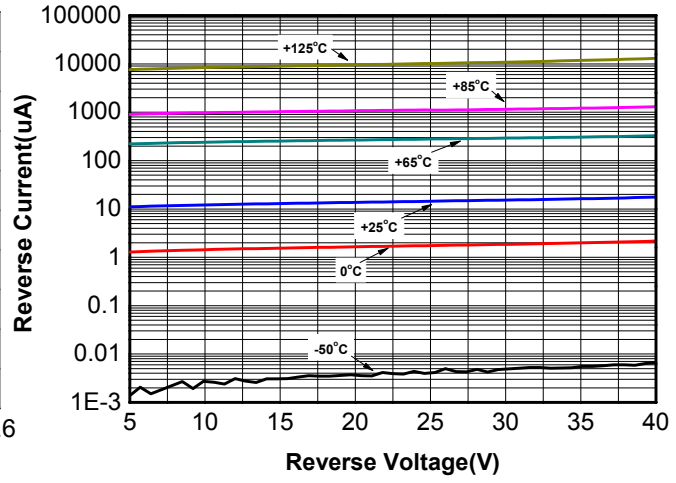


Fig.2 Reverse current vs. Reverse voltage

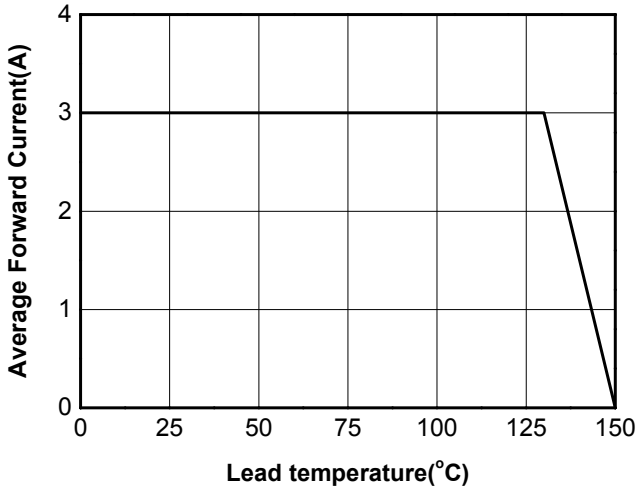


Fig.3 Maximum Forward Current Derating Curve

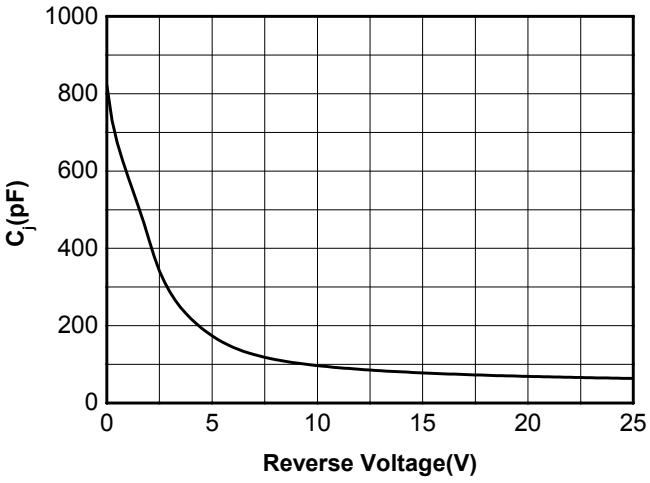
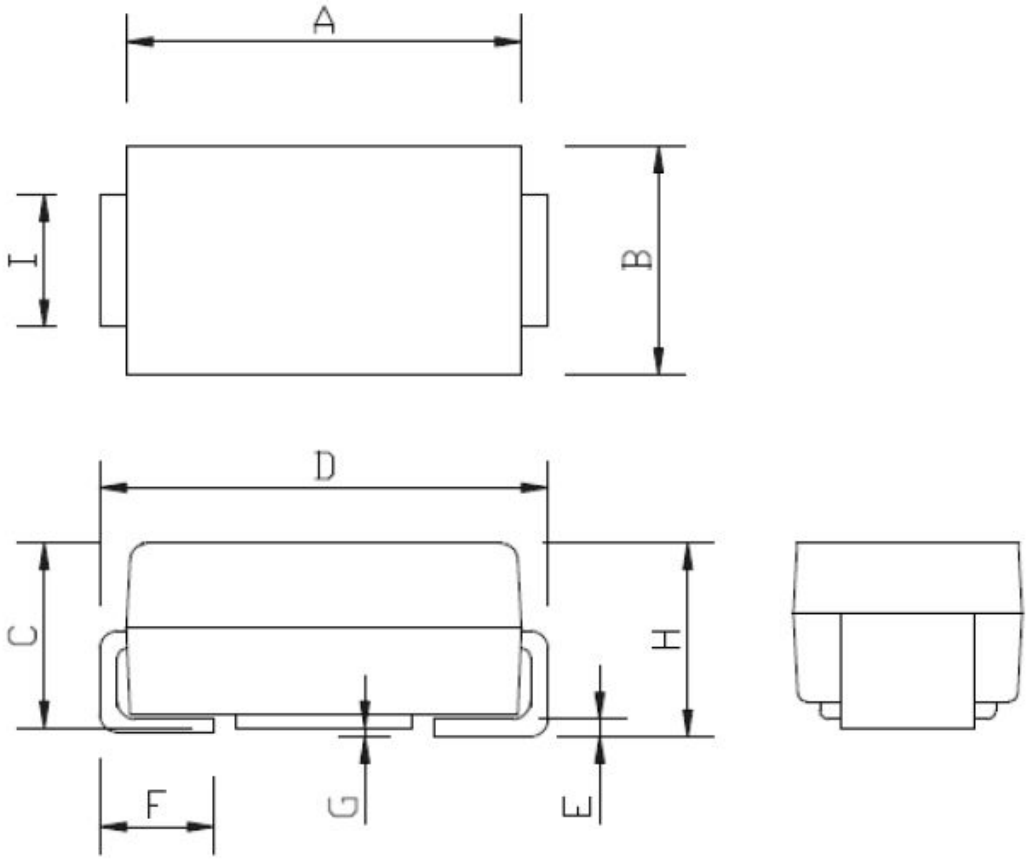


Fig.4 Junction capacitance vs. Reverse voltage

Package outline dimensions

SMA (DO-214AC)



Symbol	Dimensions in millimeter	
	Min.	Max.
A	4.25	4.65
B	2.40	2.80
C	1.85	2.15
D	4.85	5.35
E	0.10	0.30
F	0.90	1.50
G	0.20 Max.	
H	1.90	2.30
I	1.35	1.65